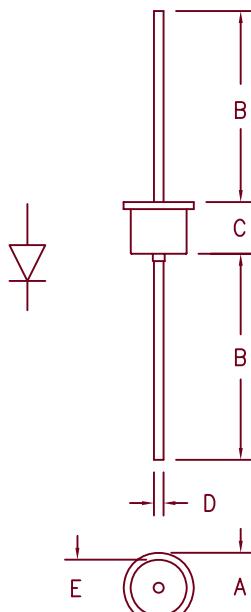
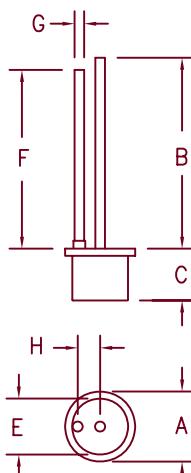


Silicon Rectifiers

1N4719-1N4725, 1N4997-1N5003



1N4719-1N4725



1N4997-1N5003

Dim.	Inches		Millimeter		
	Minimum	Maximum	Minimum	Maximum	Notes
A	---		.450	---	11.43
B	.980	---	24.89	---	
C	---	.300	---	7.62	
D	.046	.056	1.17	1.42	Dia.
E	---	.350	---	8.89	Dia.
F	.960	---	24.38	---	
G	.031	.035	.79	.89	Dia.
H	.145	.165	3.68	4.19	

Microsemi Catalog Number	Peak Reverse Voltage
1N4719, 1N4997	50V
1N4720, 1N4998	100V
1N4721, 1N4999	200V
1N4722, 1N5000	400V
1N4723, 1N5001	600V
1N4724, 1N5002	800V
1N4725, 1N5003	1000V

- High Surge Capability
- 175°C Junction Temperature
- V_{RRM} 50 to 1000 Volts
- 3 Amp Current Rating
- Hermetically Sealed

Electrical Characteristics

Average forward current
Maximum surge current
Max peak forward voltage
Max peak reverse current

I_{F(AV)} 3.0 Amps
I_{FSM} 300 Amps
V_{FM} 1.0 Volts
I_{RM} 25 μ A

T_A = 119°C, Square wave, R_{θJL} = 12°C/W, L = 1/4"
8.3ms, half sine, T_J = 175°C
I_{FM} = 3.0A; T_J = 25°C*
V_{RRM, TJ} = 25°C

*Pulse test: Pulse width 300 μ sec, Duty cycle 2%

Thermal and Mechanical Characteristics

Storage temperature range
Operating junction temp range
Maximum thermal resistance
Weight

T_{STG}
T_J
L = 1/4" R_{θJL}

-65°C to 175°C
-65°C to 175°C
12°C/W Junction to Lead
.08 ounces (2.3 grams) typical

1N4719-1N4725, 1N4997-1N5003

Figure 1
Typical Forward Characteristics

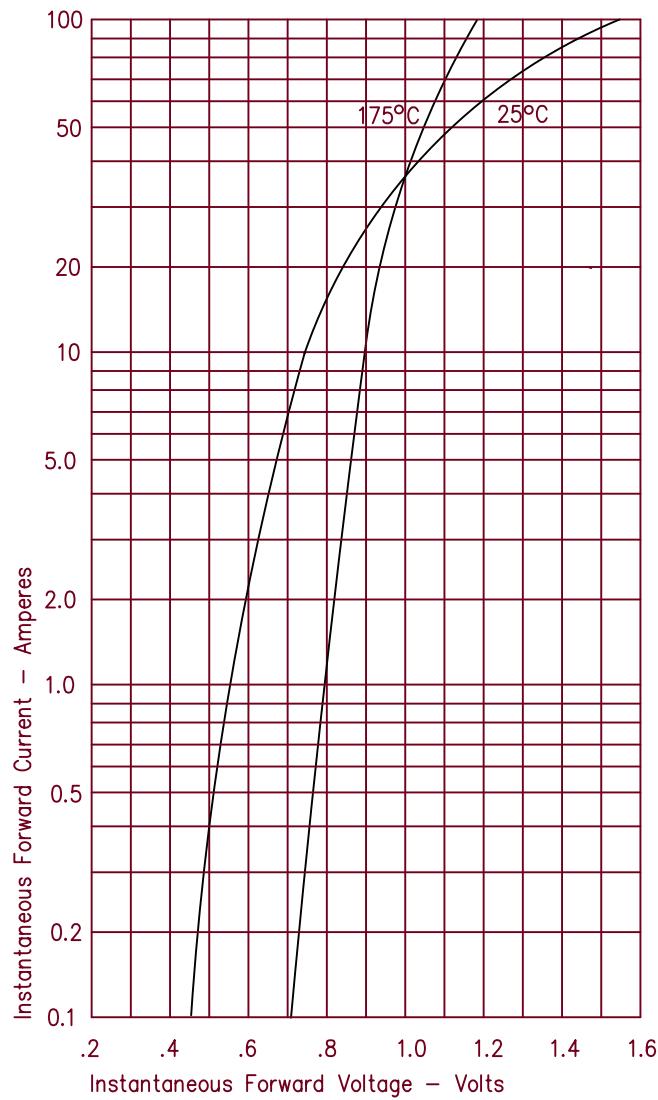


Figure 2
Typical Reverse Characteristics

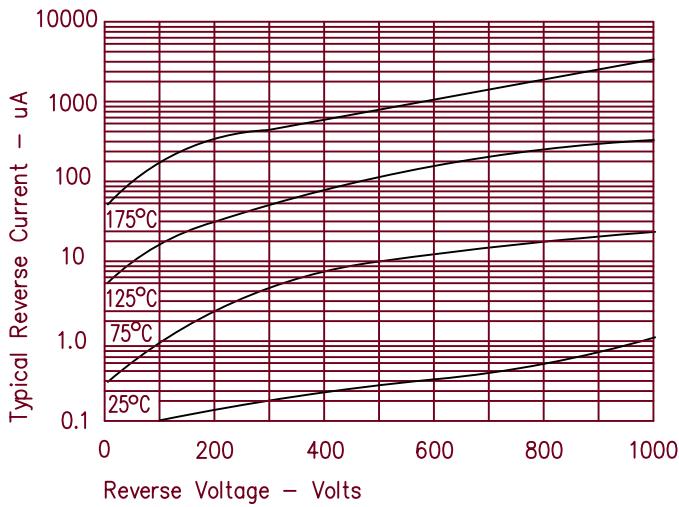


Figure 3
Forward Current Derating

